

2SC5730K

Transistors

Medium power transistor (30V, 1A)

2SC5730K

●Features

- 1) High speed switching.
(Tf : Typ. : 50ns at Ic = 1.0A)
- 2) Low saturation voltage, typically
(Typ. : 150mV at Ic = 500mA, Ib = 50mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2048K

●Applications

Small signal low frequency amplifier
High speed switching

●Structure

NPN Silicon epitaxial planar transistor

●Packaging specifications

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
2SC5730K		○

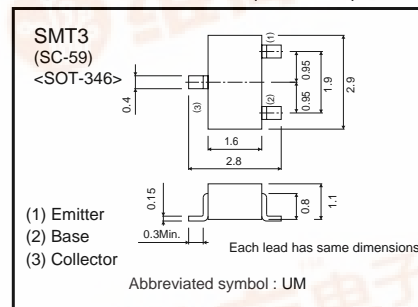
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CE0}	30	V
Emitter-base voltage	V _{EB0}	6	V
Collector current	DC	I _c	1.0 A
	Pulsed	I _{cP}	2.0 A ^{*1}
Power dissipation	P _c	200	mW ^{*2}
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to 150	°C

^{*1} P_w = 10ms

^{*2} Each terminal mounted on a recommended land

●External dimensions (Unit : mm)



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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	BV _{CEO}	30	–	–	V	I _C =1mA
Collector-base breakdown voltage	BV _{CBO}	30	–	–	V	I _C =100μA
Emitter-base breakdown voltage	BV _{EBO}	6	–	–	V	I _E =100μA
Collector cut-off current	I _{CBO}	–	–	1.0	μA	V _{CB} =20V
Emitter cut-off current	I _{EBO}	–	–	1.0	μA	V _{EB} =4V
Collector-emitter saturation voltage	V _{CE(sat)}	–	150	300	mV	I _C =500mA I _B =50mA
DC current gain	h _{FE}	120	–	390	–	V _{CE} =2V I _C =100mA
Transition frequency	f _r	–	280	–	MHz	V _{CE} =10V I _E =–100mA f=10MHz
Corrector output capacitance	C _{ob}	–	7	–	pF	V _{CB} =10V I _E =0A f=1MHz
Turn-on time	T _{on}	–	40	–	ns	I _C =1.0A I _{B1} =100mA I _{B2} =–100mA V _{CC} ≐25V
Storage time	T _{stg}	–	150	–	ns	
Fall time	T _f	–	50	–	ns	

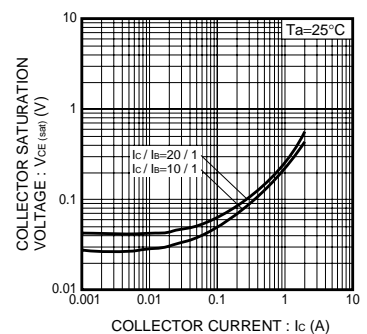
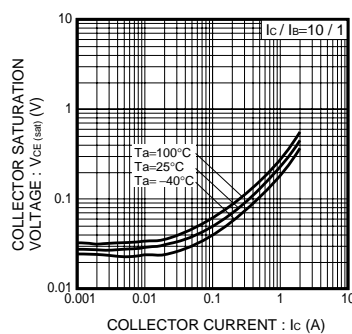
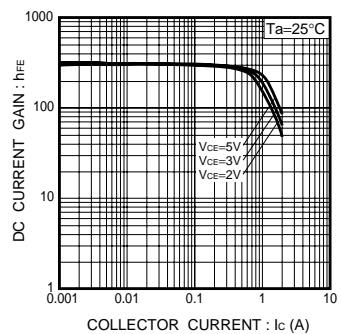
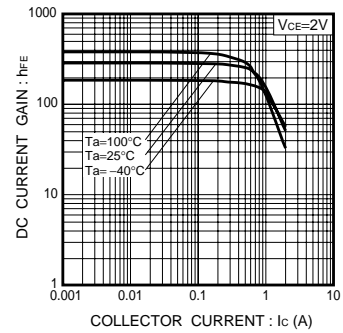
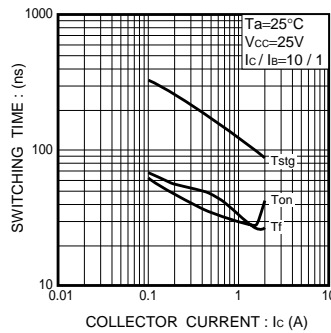
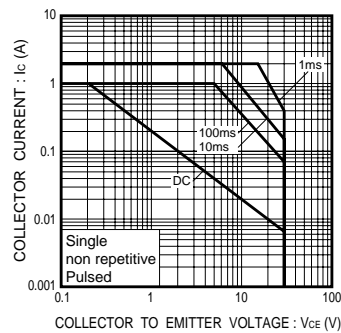
*1 Non repetitive pulse

*2 See Switching characteristics measurement circuits

●h_{FE} RANK

Q	R
120–270	180–390

●Electrical characteristic curves



Transistors

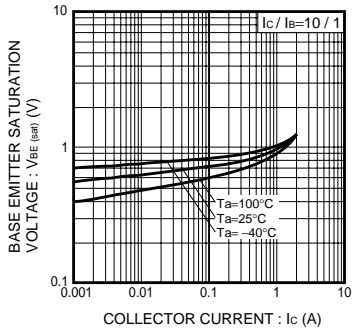


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

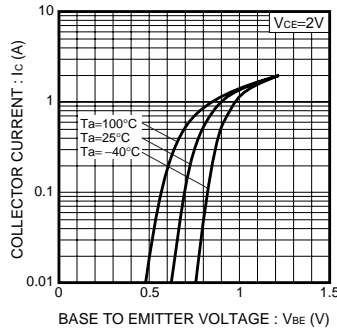


Fig.8 Grounded Emitter Propagation Characteristics

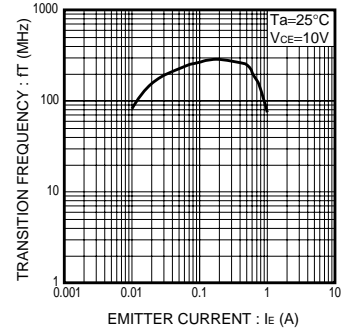


Fig.9 Transition Frequency

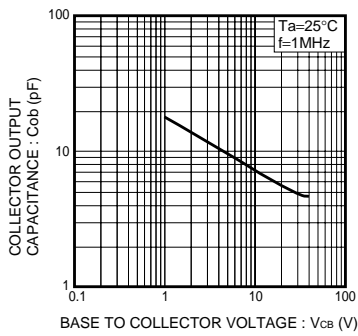
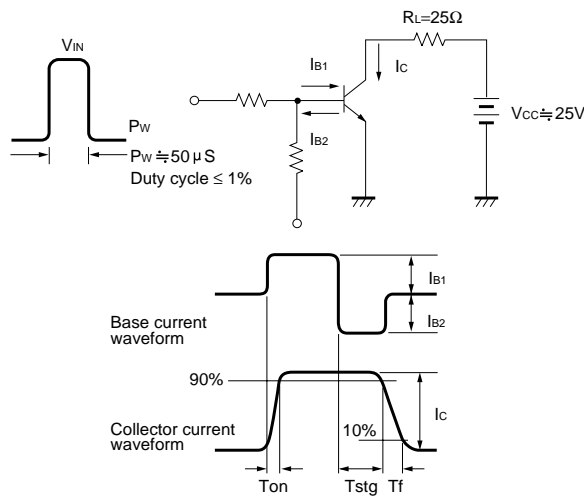


Fig.10 Collector Output Capacitance

●Switching characteristics measurement circuits



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